ABSTRACT

[0045] In one embodiment, a method including providing a semiconductor pad package having a first pad and a second pad is disclosed. A first layer comprising a first metal is deposited on the first pad using a first process. A second metal is then deposited on the first pad and the first layer using a second process. In another embodiment, the first process comprises and electroplating process, and the second process comprises a direct immersion gold (DIG) process. In a further embodiment, the first pad is a power or ground pad, and the second pad is a signal pad.